

DYNAMIC CHARACTERISTICS

APT65GP60JDQ2

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		7400		pF
C_{oes}	Output Capacitance			580		
C_{res}	Reverse Transfer Capacitance			35		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 65A$		7.5		V
Q_g	Total Gate Charge ^③			210		nC
Q_{ge}	Gate-Emitter Charge			50		
Q_{gc}	Gate-Collector ("Miller") Charge			65		
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 600V$	250			A
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 65A$ $R_G = 5\Omega$ $T_J = +25^\circ C$		30		ns
t_r	Current Rise Time			55		
$t_{d(off)}$	Turn-off Delay Time			90		
t_f	Current Fall Time			65		μJ
E_{on1}	Turn-on Switching Energy ^④			605		
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			1410		
E_{off}	Turn-off Switching Energy ^⑥			895		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 65A$ $R_G = 5\Omega$ $T_J = +125^\circ C$		30		ns
t_r	Current Rise Time			55		
$t_{d(off)}$	Turn-off Delay Time			130		
t_f	Current Fall Time			90		μJ
E_{on1}	Turn-on Switching Energy ^④			605		
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			1925		
E_{off}	Turn-off Switching Energy ^⑥			1470		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.29	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			1.21	
W_T	Package Weight		29.2		gm
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Min.)	2500			Volts

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices, I_{ces} includes both IGBT and FRED leakages
- ③ See MIL-STD-750 Method 3471.
- ④ E_{on1} is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)
- ⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)
- ⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

APT Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT65GP60JDQ2

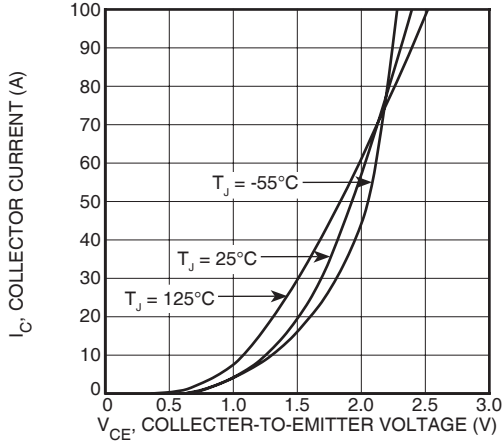


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

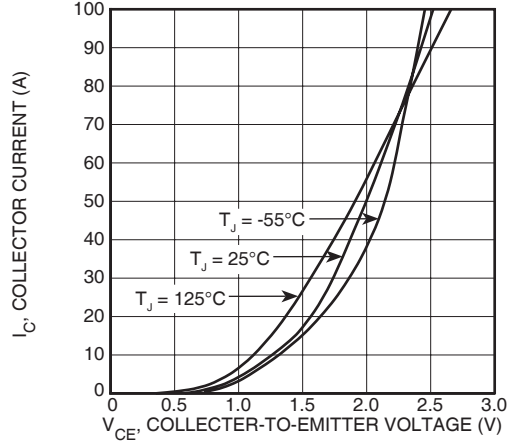


FIGURE 2, Output Characteristics ($T_J = 125^\circ\text{C}$)

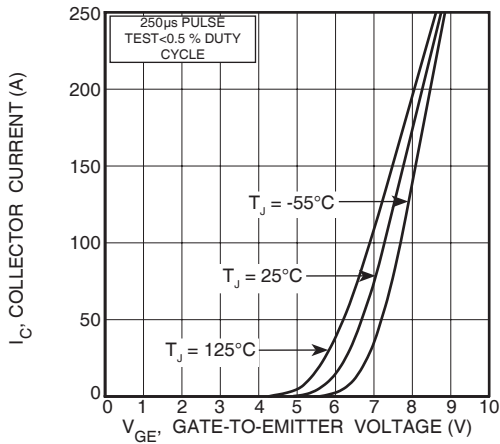


FIGURE 3, Transfer Characteristics

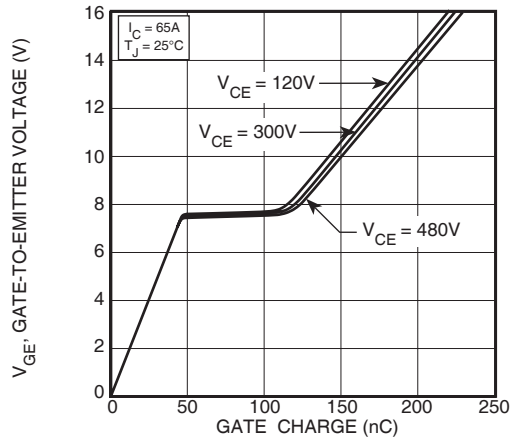


FIGURE 4, Gate Charge

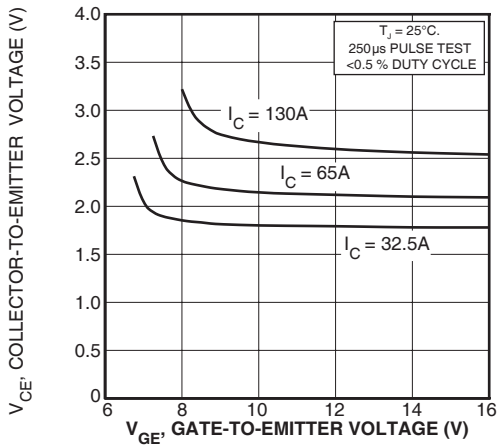


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

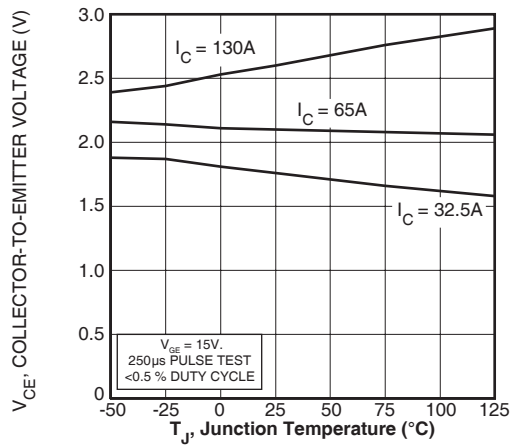


FIGURE 6, On State Voltage vs Junction Temperature

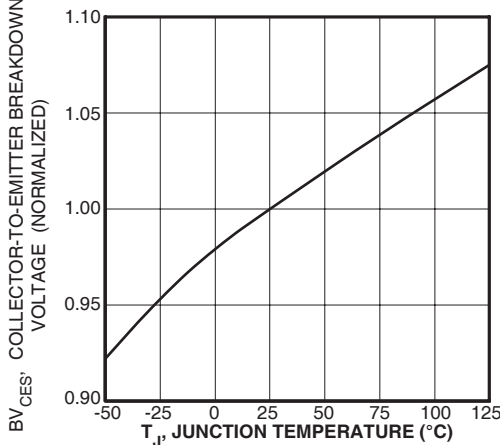


FIGURE 7, Breakdown Voltage vs. Junction Temperature

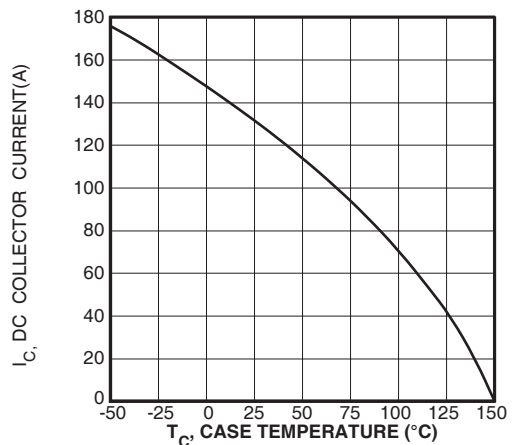


FIGURE 8, DC Collector Current vs Case Temperature

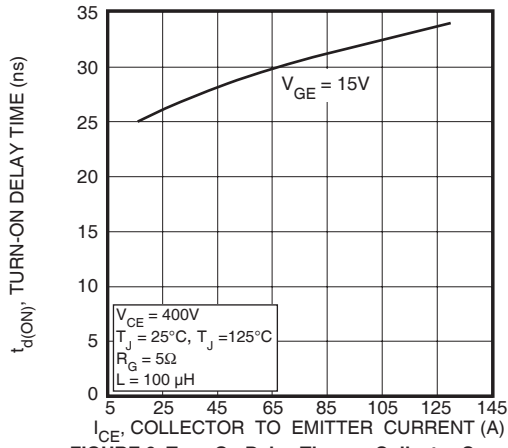


FIGURE 9, Turn-On Delay Time vs Collector Current

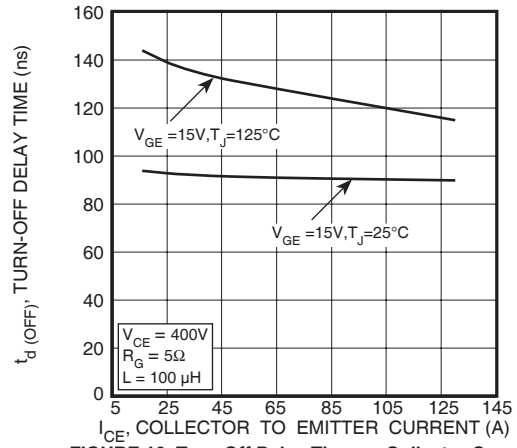


FIGURE 10, Turn-Off Delay Time vs Collector Current

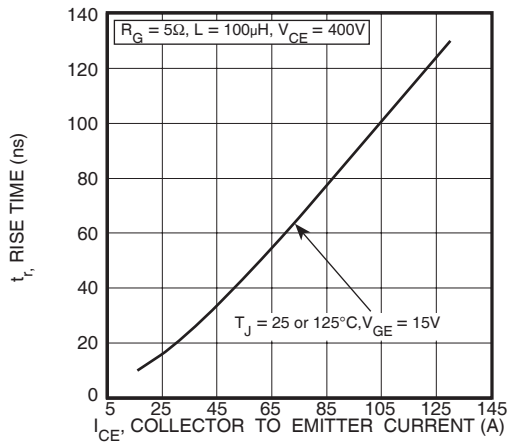


FIGURE 11, Current Rise Time vs Collector Current

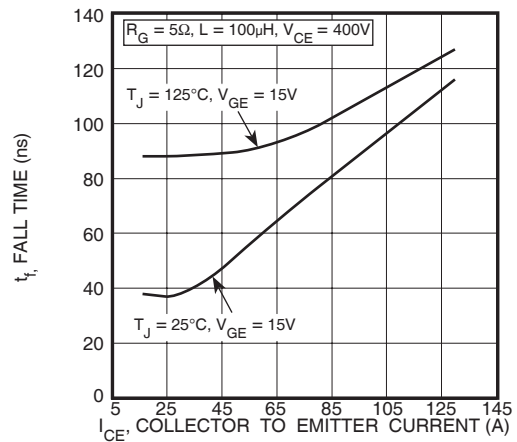


FIGURE 12, Current Fall Time vs Collector Current

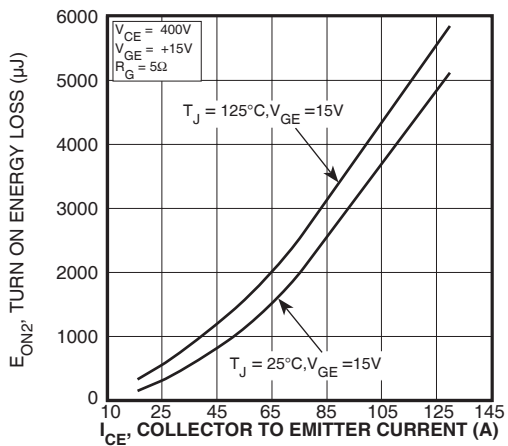


FIGURE 13, Turn-On Energy Loss vs Collector Current

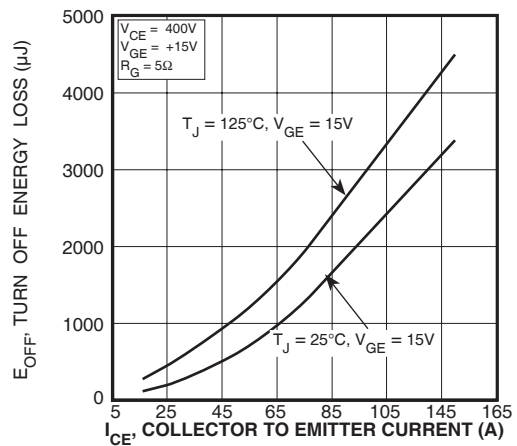


FIGURE 14, Turn Off Energy Loss vs Collector Current

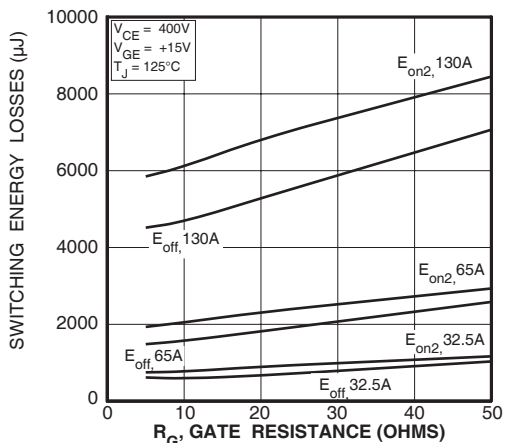


FIGURE 15, Switching Energy Losses vs. Gate Resistance

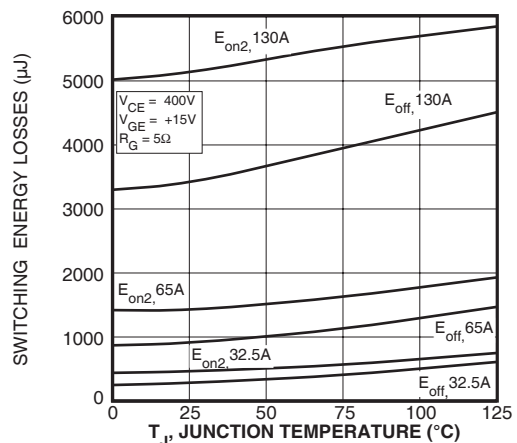


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

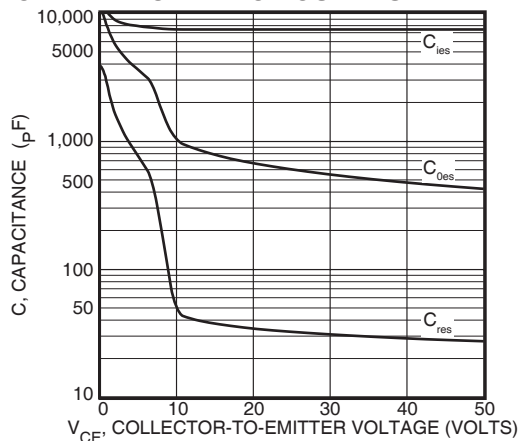


Figure 17, Capacitance vs Collector-To-Emitter Voltage

APT65GP60JDQ2

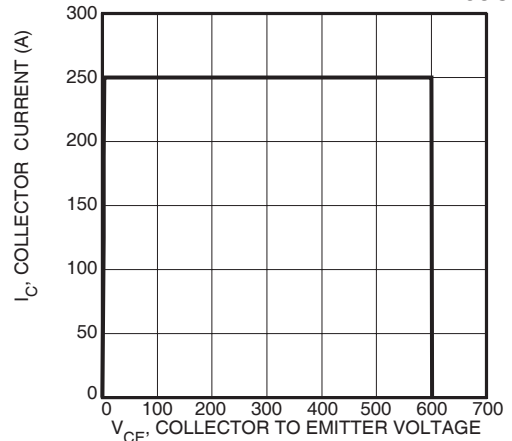


Figure 18, Minimum Switching Safe Operating Area

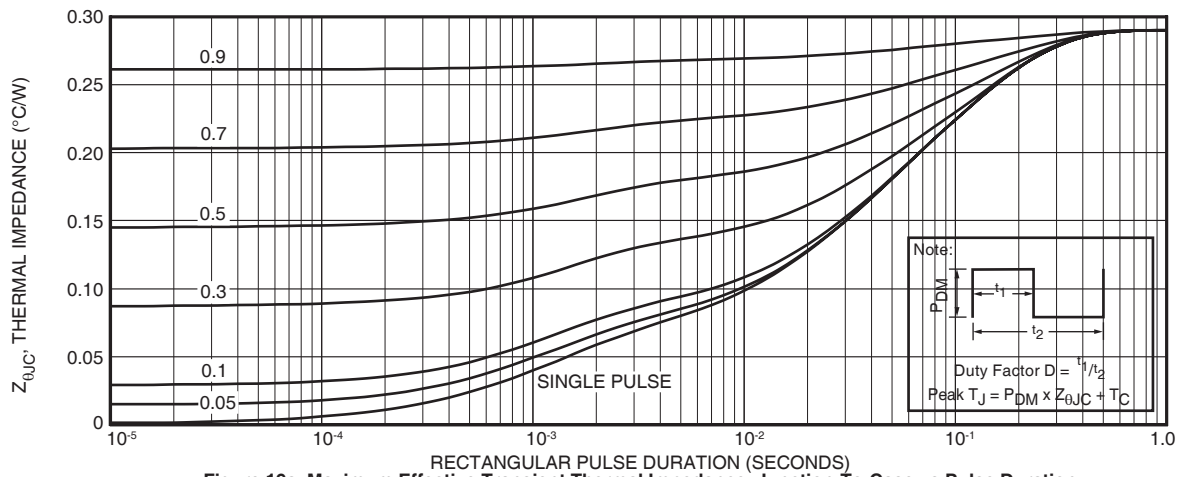


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

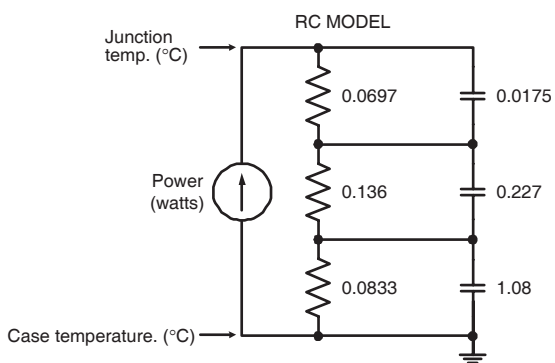


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

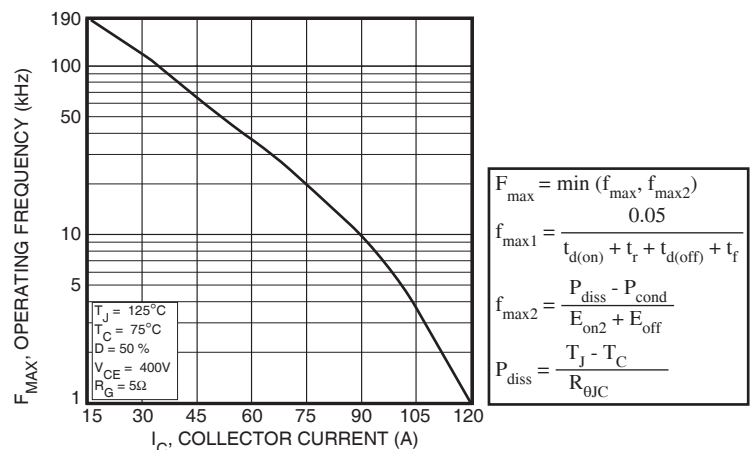


Figure 20, Operating Frequency vs Collector Current

APT65GP60JDQ2

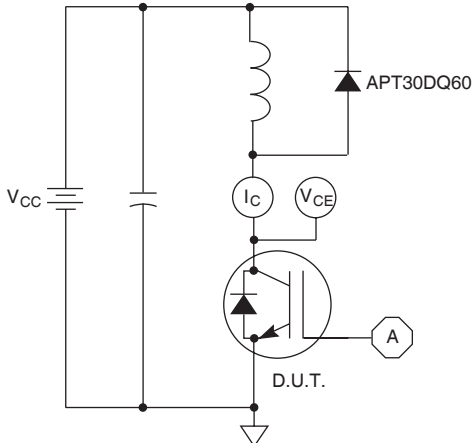


Figure 21, Inductive Switching Test Circuit

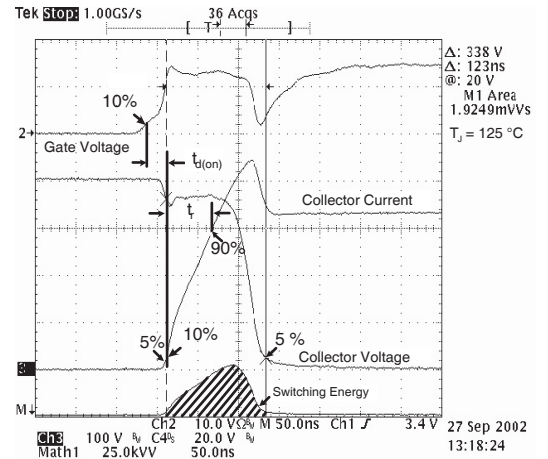


Figure 22, Turn-on Switching Waveforms and Definitions

65GP60B2 @ 125C Eoff

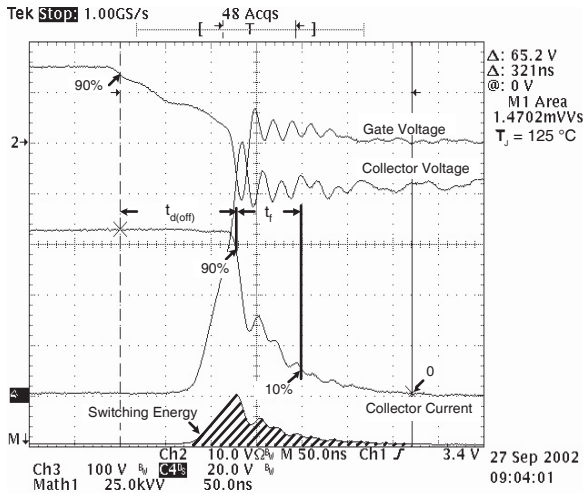


Figure 23, Turn-off Switching Waveforms and Definitions

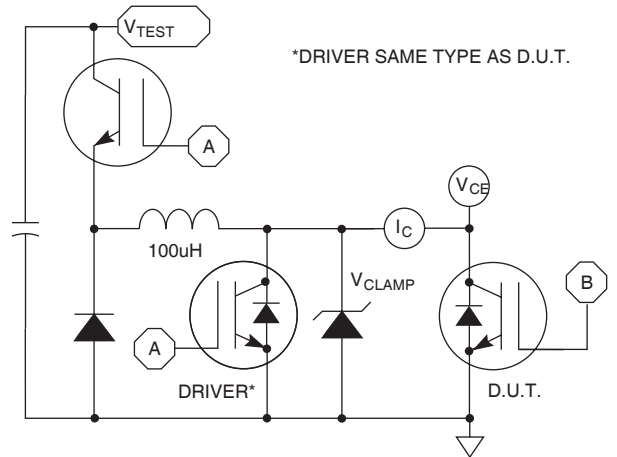


Figure 24, E_{ON1} Test Circuit

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT65GP60JDQ2		UNIT
$I_F(\text{AV})$	Maximum Average Forward Current ($T_C = 99^\circ\text{C}$, Duty Cycle = 0.5)		30	Amps
$I_F(\text{RMS})$	RMS Forward Current (Square wave, 50% duty)		42	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)		320	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage		$I_F = 65\text{A}$	2.3	Volts
			$I_F = 130\text{A}$	2.9	
			$I_F = 65\text{A}, T_J = 125^\circ\text{C}$	1.4	

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	21	-	ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	105	-	
Q_{rr}	Reverse Recovery Charge		-	115	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	3	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	125	-	ns
Q_{rr}	Reverse Recovery Charge		-	465	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	7	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	60	-	ns
Q_{rr}	Reverse Recovery Charge		-	830	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	23	-	Amps

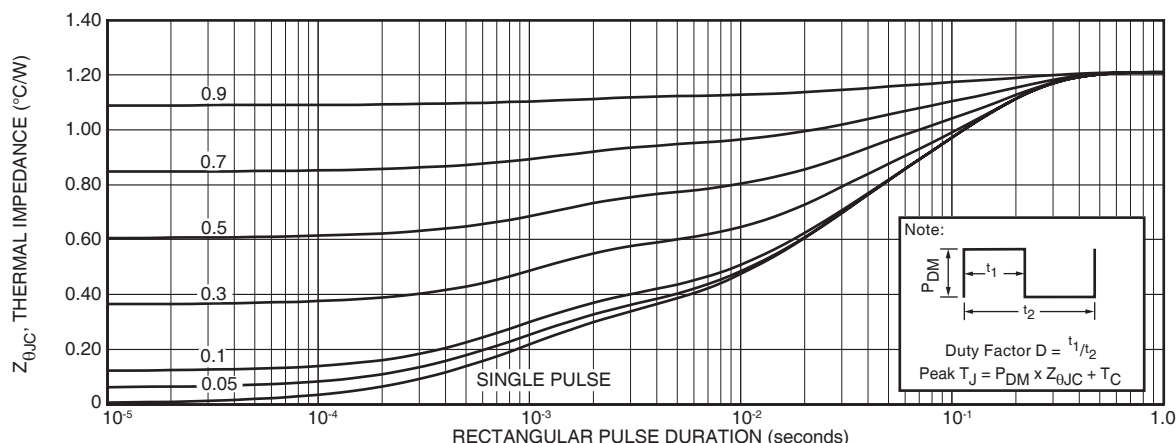


FIGURE 25a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

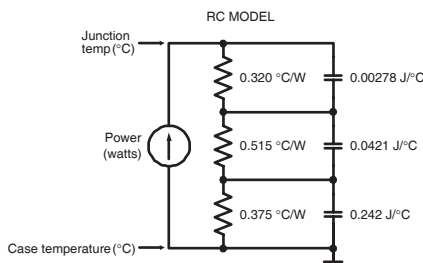


FIGURE 25b. TRANSIENT THERMAL IMPEDANCE MODEL

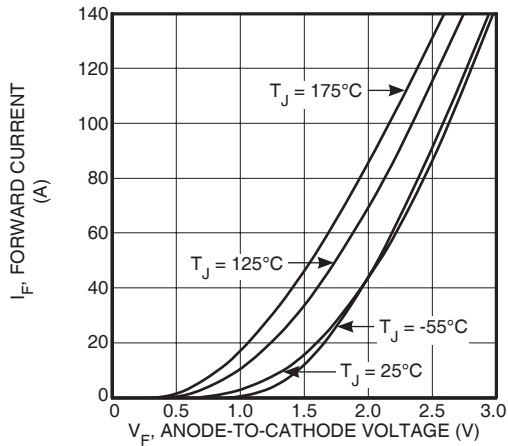


Figure 26. Forward Current vs. Forward Voltage

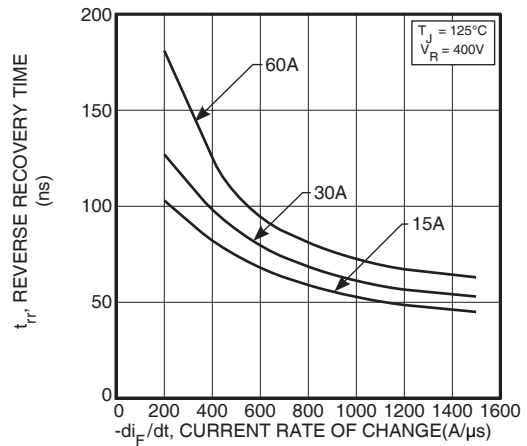


Figure 27. Reverse Recovery Time vs. Current Rate of Change

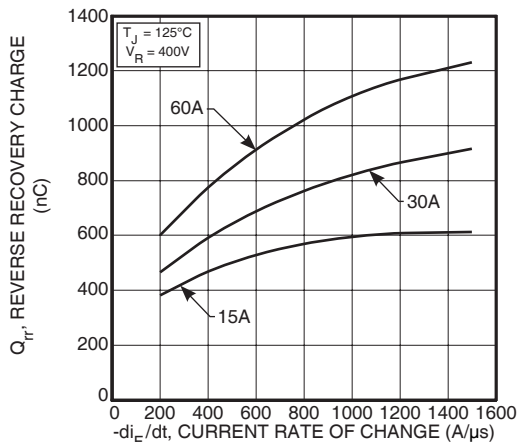


Figure 28. Reverse Recovery Charge vs. Current Rate of Change

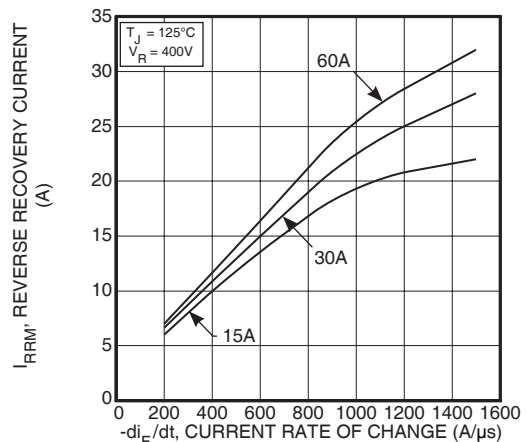


Figure 29. Reverse Recovery Current vs. Current Rate of Change

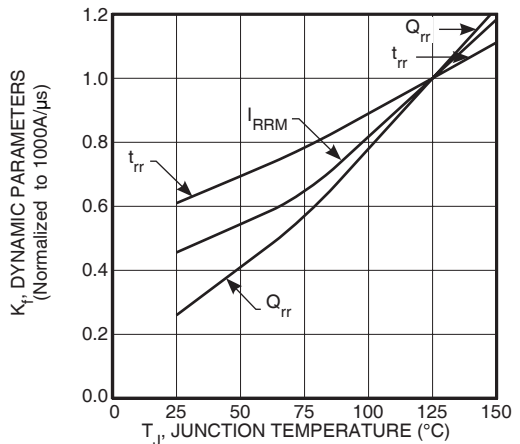


Figure 30. Dynamic Parameters vs. Junction Temperature

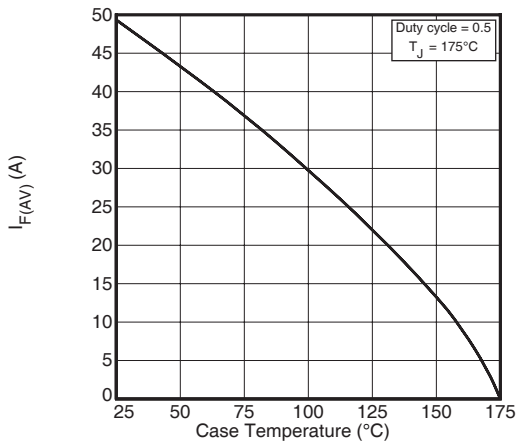


Figure 31. Maximum Average Forward Current vs. Case Temperature

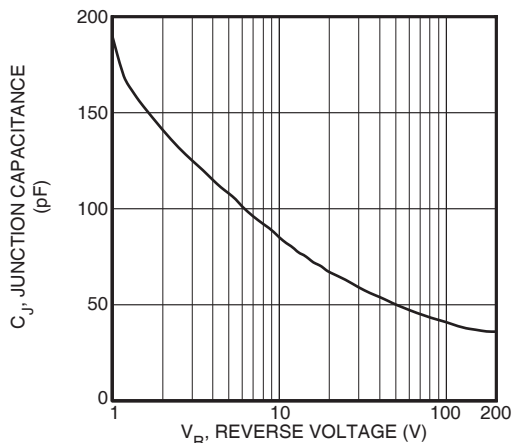


Figure 32. Junction Capacitance vs. Reverse Voltage

TYPICAL PERFORMANCE CURVES

APT65GP60JDQ2

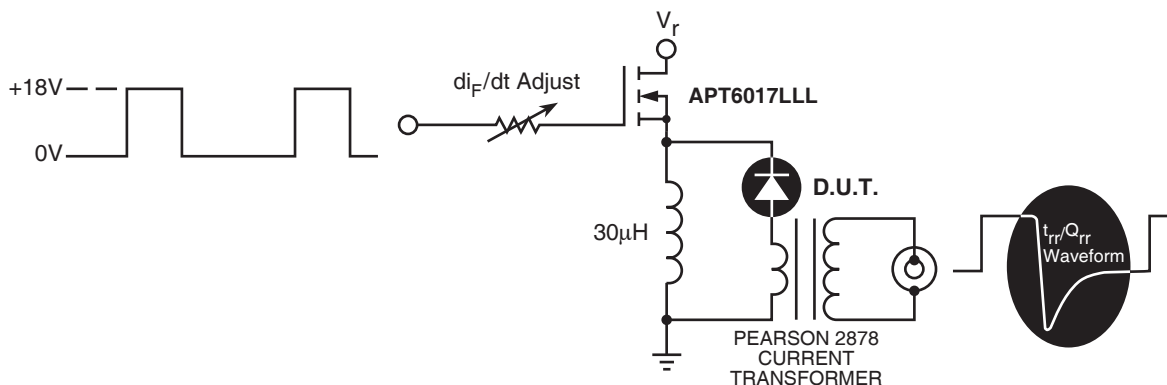


Figure 33. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

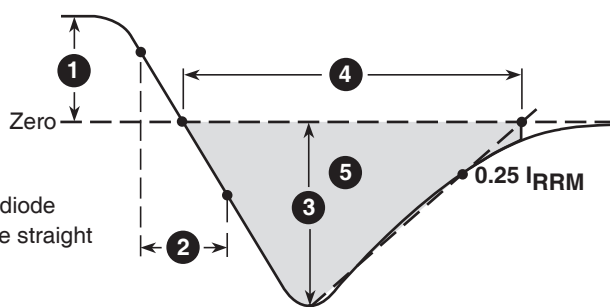
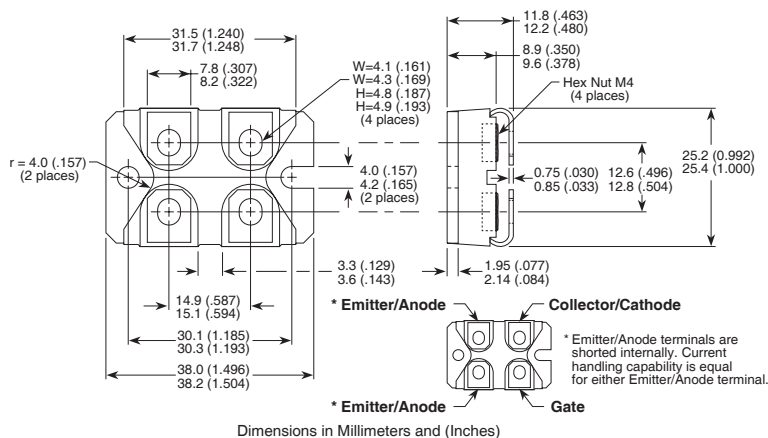


Figure 34, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



ISOTOP® is a Registered Trademark of SGS Thomson. APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.